AMENDMENT UNDER 37 C.F.R. § 1.114(c)

Application No.: 10/540,513

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the

Attorney Docket No.: Q88662

application:

LISTING OF CLAIMS:

1. (previously presented): A compound semiconductor epitaxial substrate for use in a

strain channel high electron mobility field effect transistor, comprising an InGaAs layer as a

strain channel layer and an AlGaAs layer containing n-type impurities as an electron supplying

layer, wherein said InGaAs layer has an electron mobility at room temperature of 8300 cm²/V•s

or more,

wherein undoped GaAs layers having a thickness of 4 nm or more each are laminated

respectively in contact with a top surface and a bottom surface of said strain channel layer;

wherein at least one of said undoped GaAs layers is further in contact with an undoped

AlGaAs layer; and

wherein said AlGaAs layer containing n-type impurities is in contact with said undoped

AlGaAs layer.

2. (original): The compound semiconductor epitaxial substrate according to claim 1,

wherein the InGaAs layer constituting said strain channel layer has an In composition of 0.25 or

more.

3. (canceled)

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4. (withdrawn): A method for manufacturing the compound semiconductor epitaxial

substrate according to claims 1 or 2, comprising epitaxially growing the layer of each compound

semiconductor by employing a metalorganic chemical vapor deposition (MOCVD) method.

5. (withdrawn): The method according to claim 4, wherein the InGaAs layer is

epitaxially grown as the strain channel layer such that the In composition thereof becomes 0.25

or more, the AlGaAs layer containing n-type impurities is epitaxially grown as the electron

supplying layer, and GaAs layers are each epitaxially grown to a thickness of 4 nm or more

respectively in contact with a top surface and a bottom surface of said strain channel layer.

6. (canceled).

7. (new): The compound semiconductor epitaxial substrate according to claim 1,

wherein the InGaAs layer constituting said strain channel layer has an In composition of 0.35 or

more.

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